

Silicon NPN Power Transistors

2SD1585

DESCRIPTION

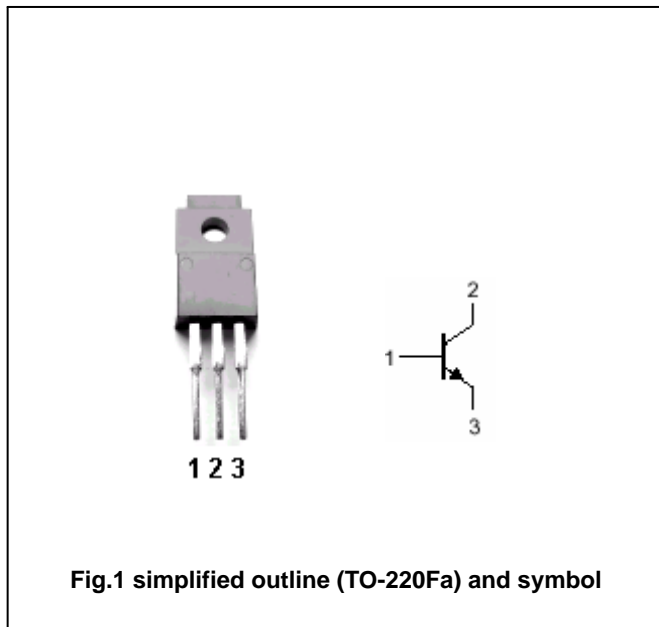
- With TO-220Fa package
- $V_{CEO}$  60V;  $V_{EBO}$  7V;  $I_{C(DC)}$  3.0A
- Complement to type 2SB1094

APPLICATIONS

- For use in audio frequency power amplifier and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings( $T_a=25$  )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	60	V
$V_{CEO}$	Collector -emitter voltage	Open base	60	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		3	A
$I_{CM}$	Collector current-Peak		5	A
$I_B$	Base current		0.6	A
$P_C$	Collector power dissipation	$T_a=25$	2.0	W
		$T_C=25$	15	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =30mA; I <sub>B</sub> =0	60			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.2A			1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.2A			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =60V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =50mA; V <sub>CE</sub> =5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =0.5A; V <sub>CE</sub> =5V	40		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A; V <sub>CE</sub> =5V		16		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz; V <sub>CB</sub> =10V		48		pF

◆ h<sub>FE-2</sub> Classifications

M	L	K
40-80	60-120	100-200

PACKAGE OUTLINE

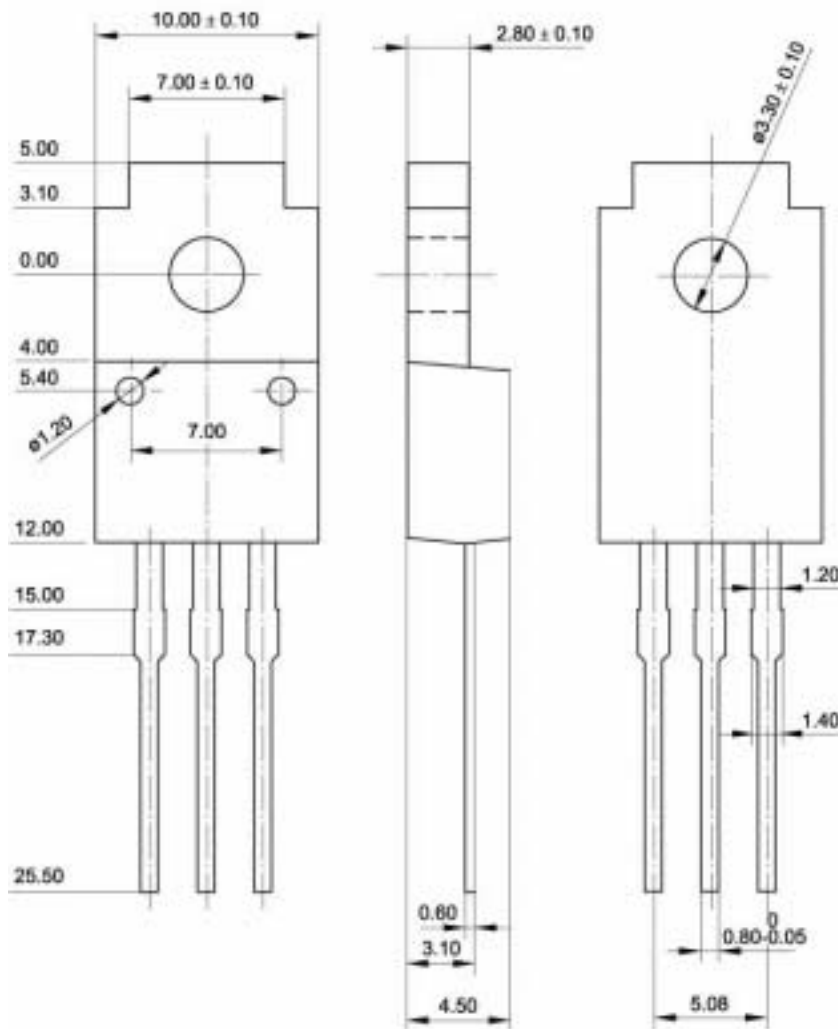


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)